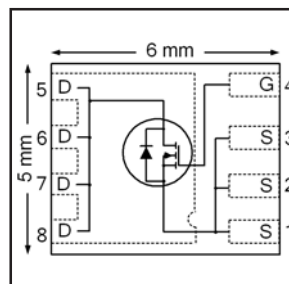


# IRFH5004PbF

HEXFET® Power MOSFET

<b>V<sub>DS</sub></b>	<b>40</b>	<b>V</b>
<b>R<sub>DS(on)</sub> max</b> (@ V <sub>GS</sub> = 10V)	<b>2.6</b>	<b>mΩ</b>
<b>Q<sub>g</sub> (typical)</b>	<b>73</b>	<b>nC</b>
<b>R<sub>G</sub> (typical)</b>	<b>1.2</b>	<b>Ω</b>
<b>I<sub>D</sub></b> (@ T <sub>mb</sub> = 25°C)	<b>100</b> ⑥	<b>A</b>



PQFN 5X6 mm

## Applications

- Secondary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

## Features and Benefits

### Features

Low R <sub>DS(on)</sub> (≤ 2.6mΩ)
Low Thermal Resistance to PCB (≤ 0.8°C/W)
100% R <sub>g</sub> tested
Low Profile (≤ 0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

results in



### Benefits

Lower Conduction Losses
Enables better thermal dissipation
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRFH5004PBF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH5004TRPBF
	PQFN 5mm x 6mm	Tape and Reel	1000	IRFH5004TR2PBF

## Absolute Maximum Ratings

	Parameter	Max.	Units
V <sub>DS</sub>	Drain-to-Source Voltage	40	V
V <sub>GS</sub>	Gate-to-Source Voltage	±20	
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	28	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	23	
I <sub>D</sub> @ T <sub>mb</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	100 ⑥	
I <sub>D</sub> @ T <sub>mb</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	100 ⑥	
I <sub>DM</sub>	Pulsed Drain Current ①	400	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation ⑤	3.6	W
P <sub>D</sub> @ T <sub>mb</sub> = 25°C	Power Dissipation ⑤	156	
	Linear Derating Factor ⑤	0.029	W/°C
T <sub>J</sub>	Operating Junction and	-55 to + 150	°C
T <sub>STG</sub>	Storage Temperature Range		

Notes ① through ⑥ are on page 8

Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.04	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.1	2.6	m $\Omega$	$V_{GS} = 10V, I_D = 50A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 150\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-5.6	—	mV/ $^\circ\text{C}$	
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
gfs	Forward Transconductance	91	—	—	S	$V_{DS} = 15V, I_D = 50A$
$Q_g$	Total Gate Charge	—	73	110	nC	$V_{DS} = 20V$ $V_{GS} = 10V$ $I_D = 50A$ See Fig.17 & 18
$Q_{gs1}$	Pre-Vth Gate-to-Source Charge	—	15	—		
$Q_{gs2}$	Post-Vth Gate-to-Source Charge	—	6.1	—		
$Q_{gd}$	Gate-to-Drain Charge	—	27	—		
$Q_{godr}$	Gate Charge Overdrive	—	25	—		
$Q_{sw}$	Switch Charge ( $Q_{gs2} + Q_{gd}$ )	—	33.1	—		
$Q_{oss}$	Output Charge	—	27	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
$R_G$	Gate Resistance	—	1.2	—	$\Omega$	
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	$V_{DD} = 20V, V_{GS} = 10V$ $I_D = 50A$ $R_G = 1.8\Omega$ See Fig.15
$t_r$	Rise Time	—	39	—		
$t_{d(off)}$	Turn-Off Delay Time	—	28	—		
$t_f$	Fall Time	—	16	—		
$C_{iss}$	Input Capacitance	—	4490	—	pF	$V_{GS} = 0V$ $V_{DS} = 20V$ $f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	970	—		
$C_{rss}$	Reverse Transfer Capacitance	—	460	—		

## Avalanche Characteristics

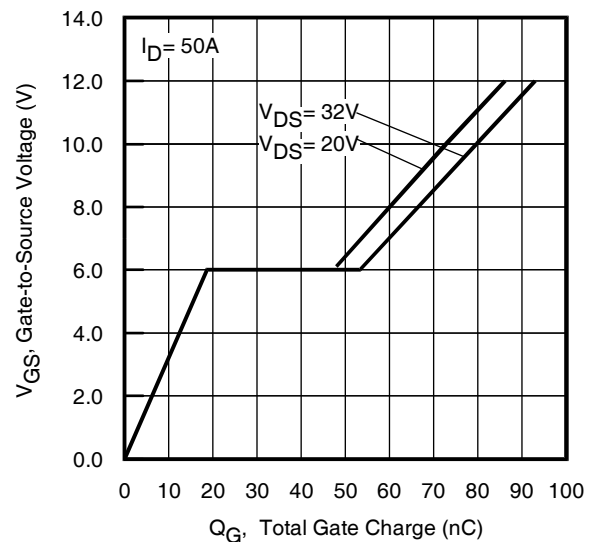
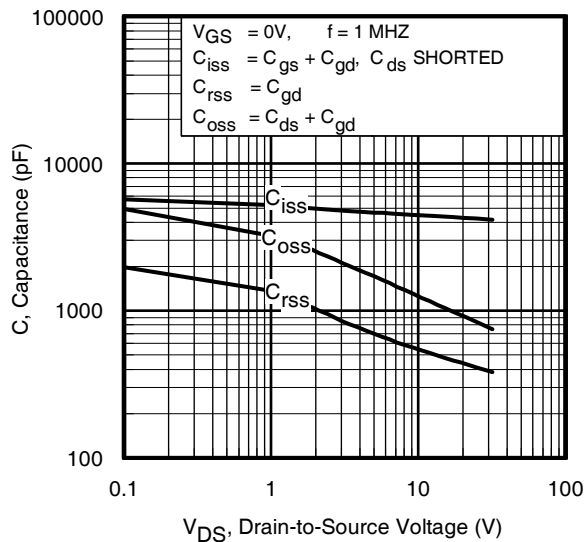
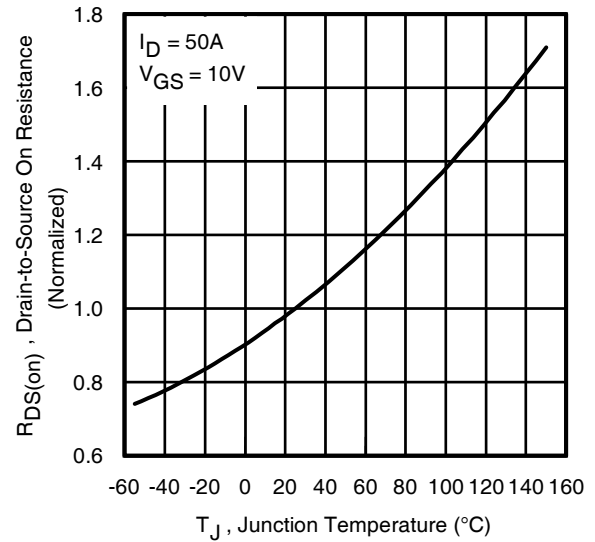
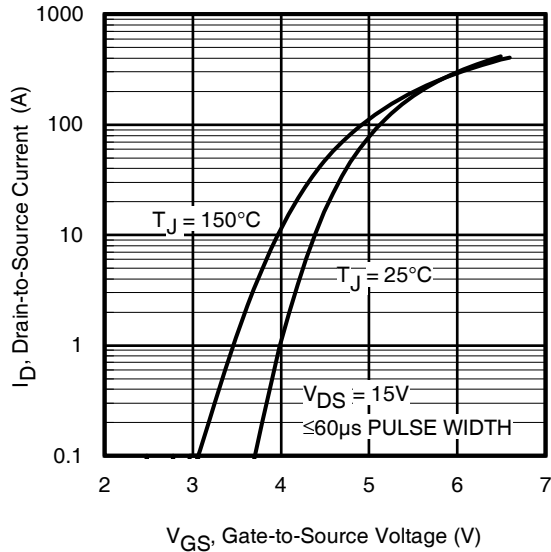
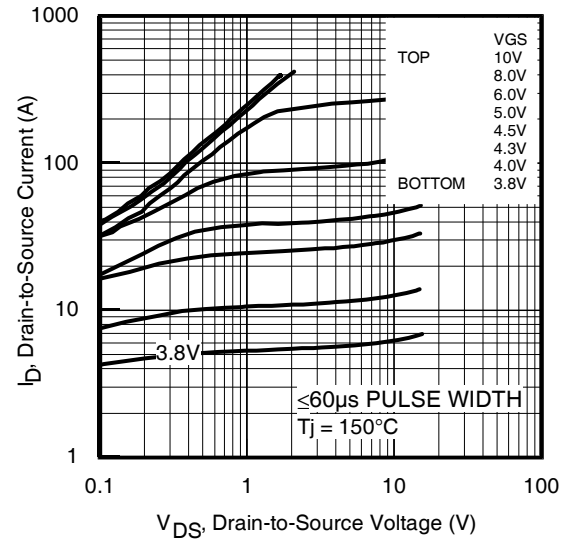
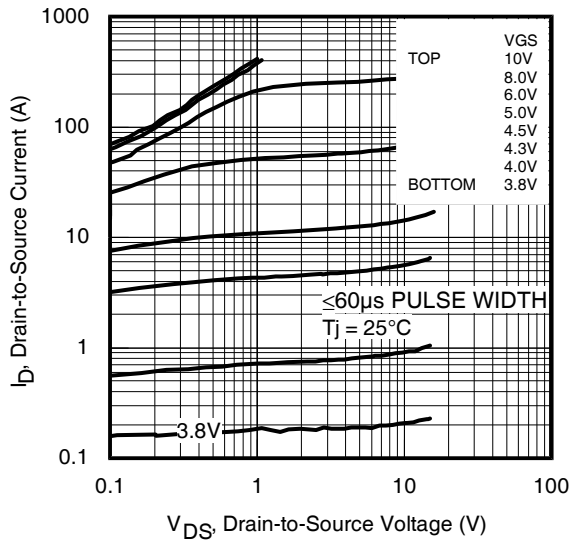
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy ②	—	340	mJ
$I_{AR}$	Avalanche Current ①	—	50	A

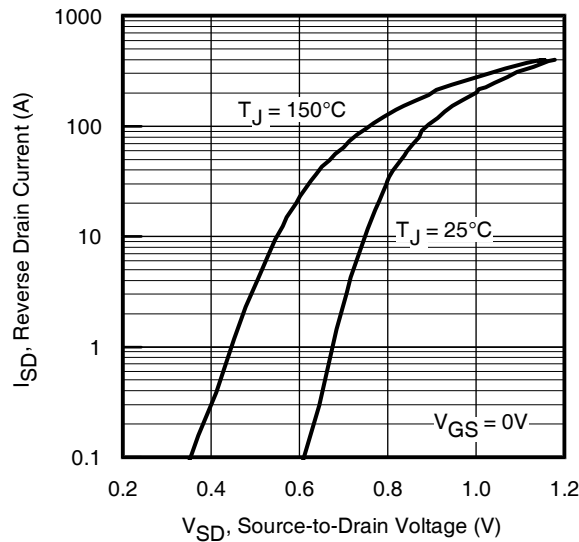
## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode) ⑥	—	—	100	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	400		
$V_{SD}$	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 50A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	32	48	ns	$T_J = 25^\circ\text{C}, I_F = 50A, V_{DD} = 20V$
$Q_{rr}$	Reverse Recovery Charge	—	100	150	nC	$di/dt = 300A/\mu s$ ③
$t_{on}$	Forward Turn-On Time	Time is dominated by parasitic Inductance				

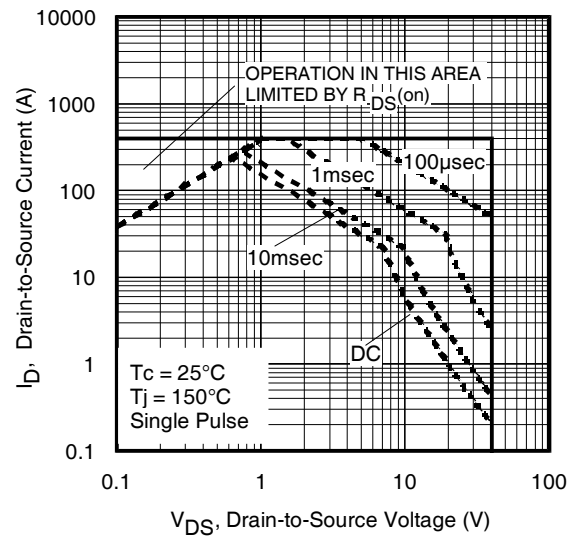
## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC-mb}$	Junction-to-Mounting Base	0.5	0.8	$^\circ\text{C/W}$
$R_{\theta JC}$ (Top)	Junction-to-Case ④	—	15	
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	35	
$R_{\theta JA} (<10s)$	Junction-to-Ambient ⑤	—	33	

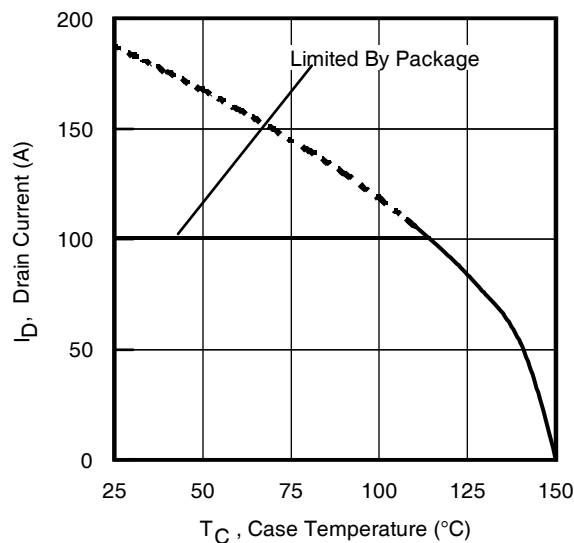




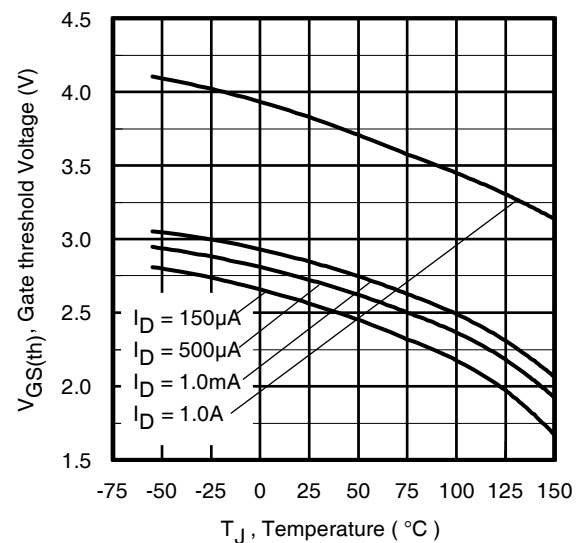
**Fig 7.** Typical Source-Drain Diode Forward Voltage



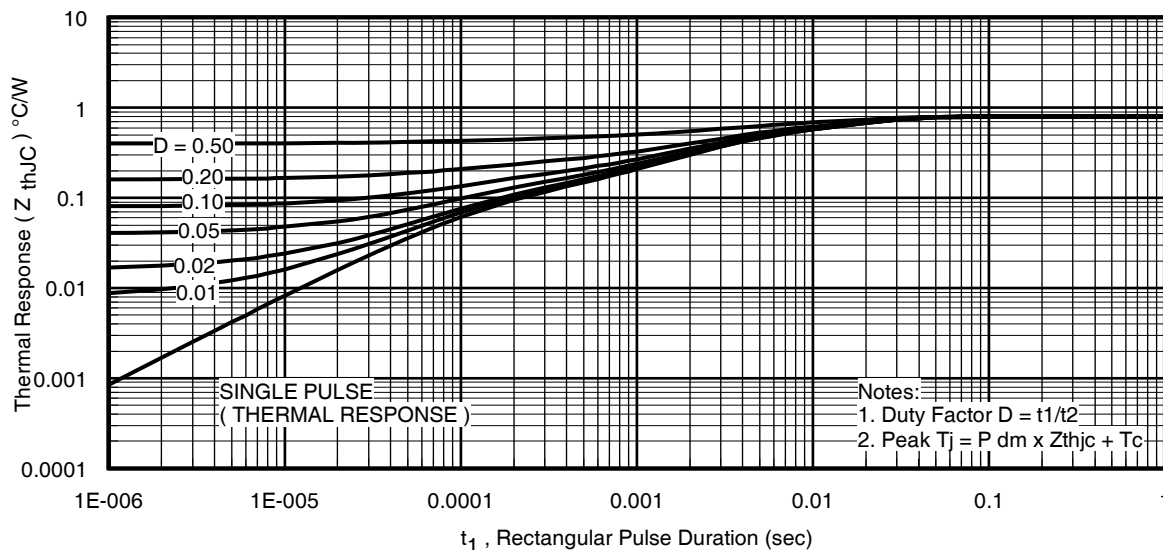
**Fig 8.** Maximum Safe Operating Area



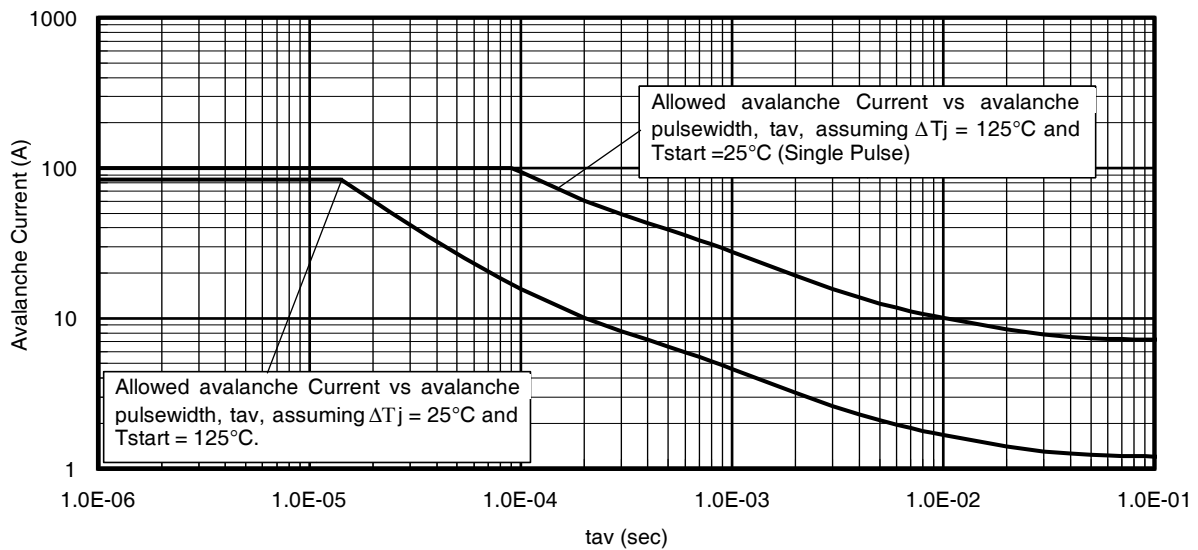
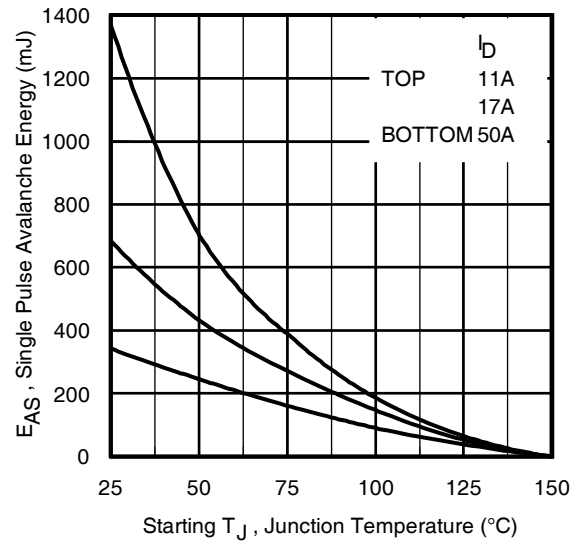
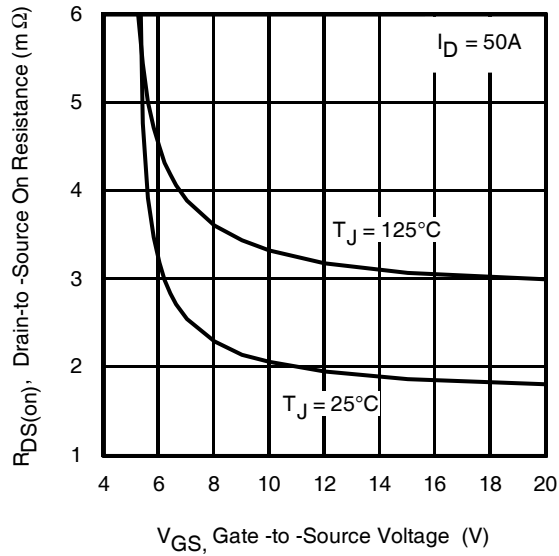
**Fig 9.** Maximum Drain Current vs. Case Temperature

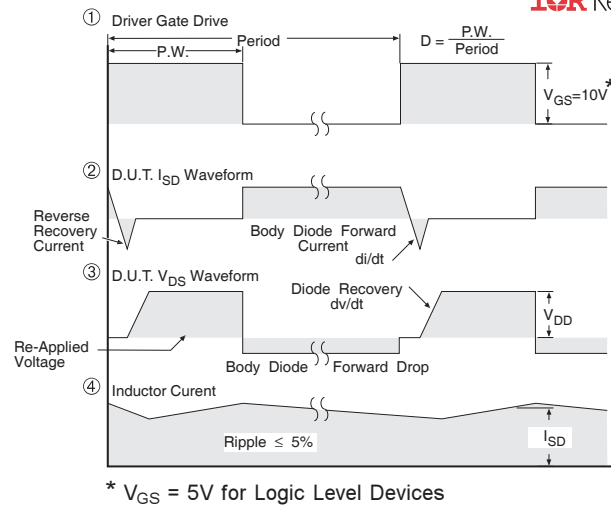
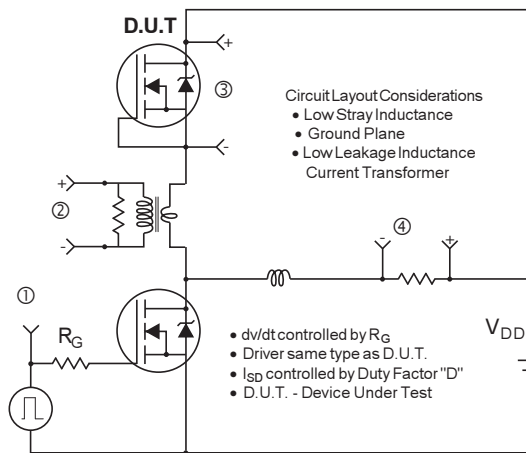


**Fig 10.** Threshold Voltage vs. Temperature

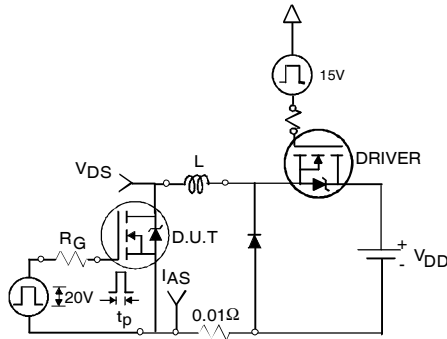


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Mounting Base

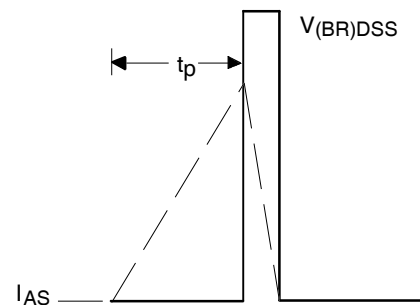




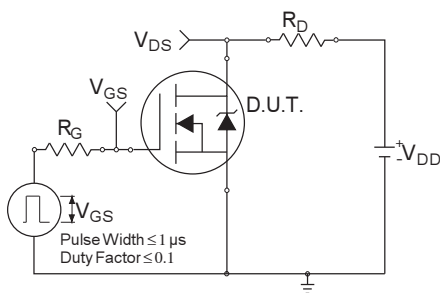
**Fig 15. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



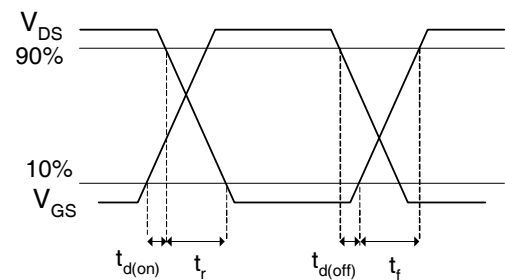
**Fig 16a. Unclamped Inductive Test Circuit**



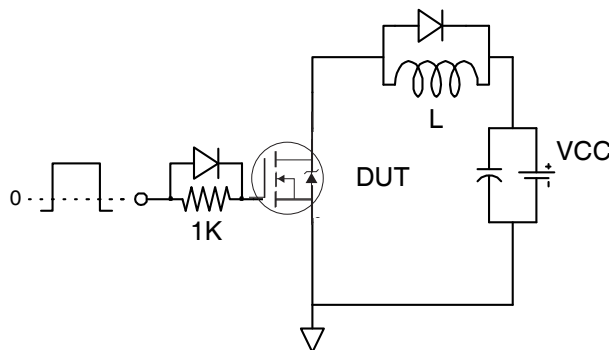
**Fig 16b. Unclamped Inductive Waveforms**



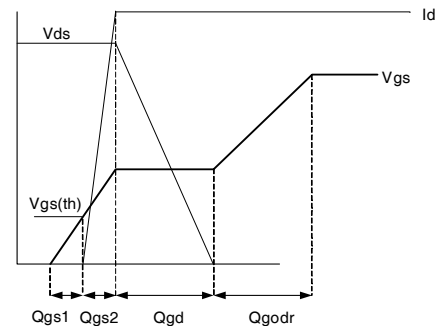
**Fig 17a. Switching Time Test Circuit**



**Fig 17b. Switching Time Waveforms**

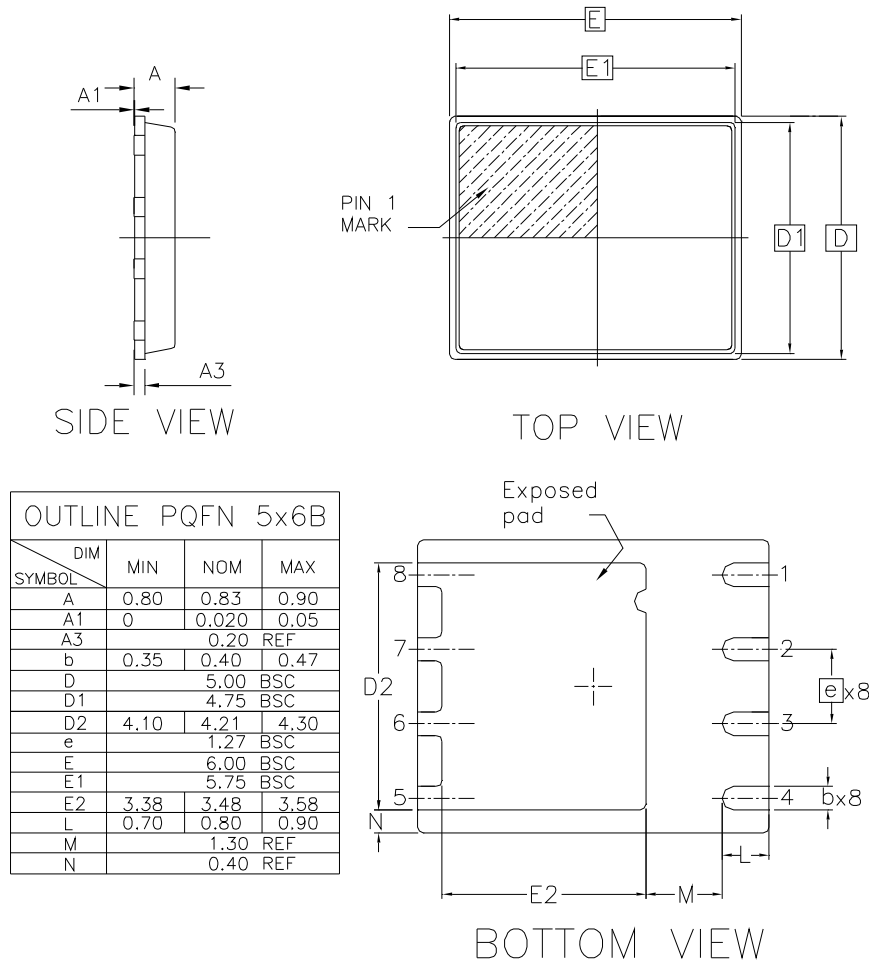


**Fig 18a. Gate Charge Test Circuit**



**Fig 18b. Gate Charge Waveform**

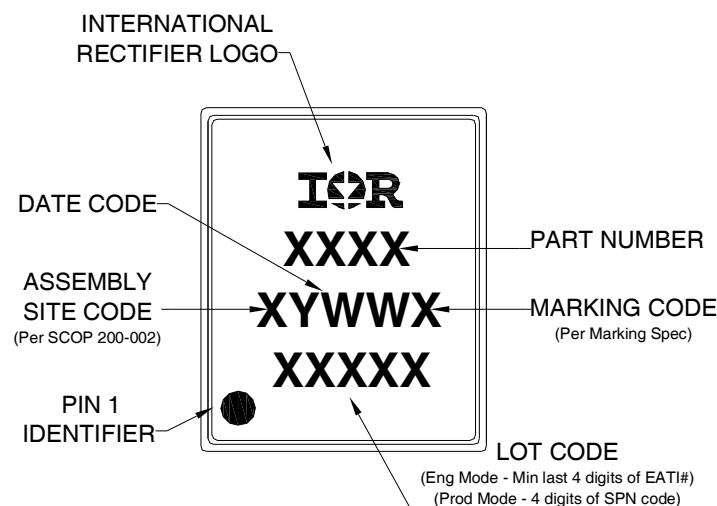
## PQFN 5x6 Outline "B" Package Details



For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

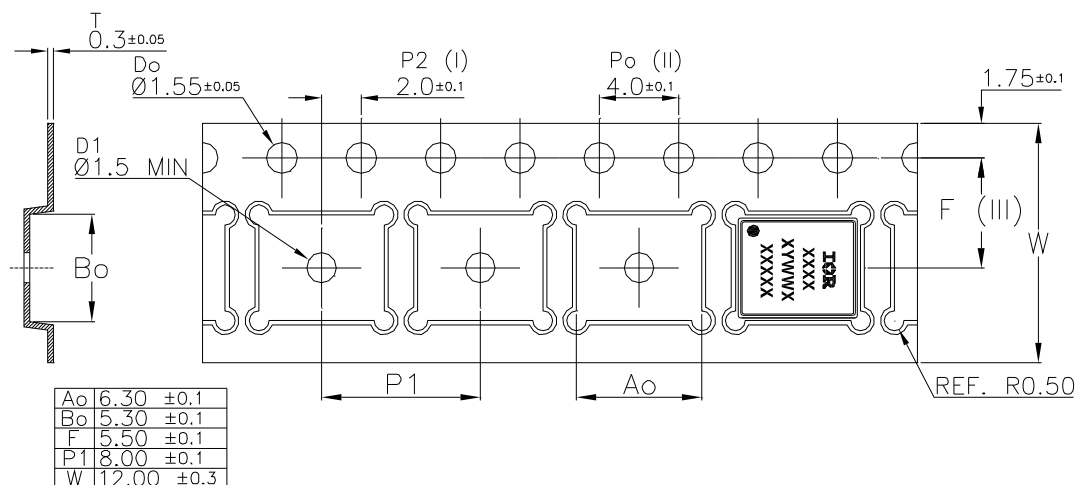
For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

## PQFN 5x6 Outline "B" Part Marking



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>  
www.irf.com

## PQFN 5x6 Outline "B" Tape and Reel

Qualification information<sup>†</sup>

Qualification level	Industrial <sup>††</sup> (per JEDEC JESD47F <sup>†††</sup> guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D <sup>†††</sup> )
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

## Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.27\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 50\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package is limited to 100A by production test capability.

Data and specifications subject to change without notice.

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